TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

### TC74HC4051AP,TC74HC4051AF,TC74HC4051AFT TC74HC4052AP,TC74HC4052AF,TC74HC4052AFT TC74HC4053AP,TC74HC4053AF,TC74HC4053AFN,TC74HC4053AFT

TC74HC4051AP/AF/AFT

8-Channel Analog Multiplexer/Demulitiplexer

TC74HC4052AP/AF/AFT

Dual 4-Channel Analog Multiplexer/Demultiplexer

TC74HC4053AP/AF/AFN/AFT

Triple 2-Channel Analog Multiplexer/Demultiplexer

The TC74HC4051A/4052A/4053A are high speed CMOS ANALOG MULTIPLEXER/DEMULTIPLEXER fabricated with silicon gate C<sup>2</sup>MOS technology. They achieve the high speed operation similar to equivalent LSTTL while maintaining the CMOS low power dissipation.

The TC74HC4051A has an 8 channel configuration, the TC74HC4052A has a 4 channel × 2 configuration and the TC74HC4053A has a 2 channel × 3 configuration.

The digital signal to the control terminal turns "ON" the corresponding switch of each channel a large amplitude signal  $(V_{CC} - V_{EE})$  can then be switched by the small logical amplitude  $(V_{CC} - GND)$  control signal.

For example, in the case of  $V_{CC} = 5 V$ , GND = 0 V,  $V_{EE} = -5 V$ , signals between -5 V and +5 V can be switched from the logical circuit with a single power supply of 5 V. As the ON-resistance of each switch is low, they can be connected to circuits with low input impedance.

All inputs are equipped with protection circuits against static discharge or transient excess voltage.

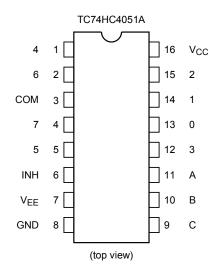
#### Features

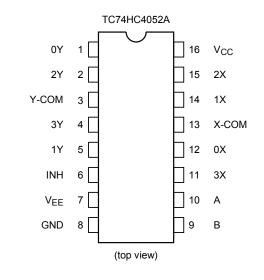
- High speed:  $t_{pd} = 15 \text{ ns}$  (typ.) at  $V_{CC} = 5 \text{ V}$ ,  $V_{EE} = 0 \text{ V}$
- Low power dissipation:  $ICC = 4 \mu A (max)$  at  $Ta = 25^{\circ}C$
- High noise immunity: VNIH = VNIL = 28% VCC (min)
- Low ON resistance:  $R_{ON} = 50 \Omega$  (typ.) at  $V_{CC} V_{EE} = 9 V$
- High noise immunity: THD = 0.02% (typ.) at V<sub>CC</sub> V<sub>EE</sub> = 9 V
- Pin and function compatible with 4051/4052/4053B

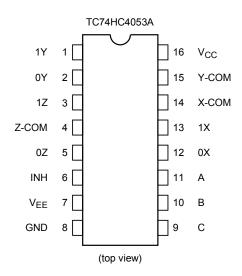
Weight	
DIP16-P-300-2.54A	: 1.00 g (typ.)
SOP16-P-300-1.27A	: 0.18 g (typ.)
SOP16-P-300-1.27	: 0.18 g (typ.)
SOL16-P-150-1.27	: 0.13 g (typ.)
TSSOP16-P-0044-0.65A	: 0.06 g (typ.)

Note: xxxFN (JEDEC SOP) is not available in Japan TC74HC4051AP, TC74HC4052AP, TC74HC4053AP DIP16-P-300-2.54A TC74HC4051AF, TC74HC4052AF, TC74HC4053AF SOP16-P-300-1.27A न्मममम SOP16-P-300-1.27 TC74HC4053AFN SOL16-P-150-1.27 TC74HC4051AFT, TC74HC4052AFT, TC74HC4053AFT TSSOP16-P-0044-0.65A

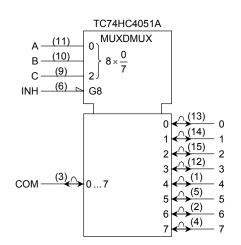
## **Pin Assignment**

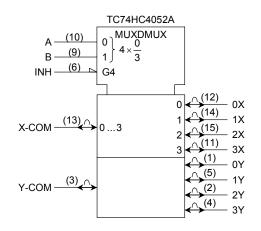


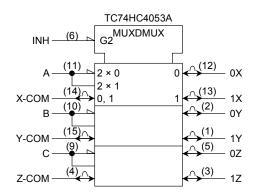




## IEC Logic Symbol







#### **Truth Table**

	Control	Inputs		"ON" Channel				
Inhibit	C*	В	А	HC4051A	HC4052A	HC4053A		
L	L	L	L	0	0X, 0Y	0X, 0Y, 0Z		
L	L	L	Н	1	1X, 1Y	1X, 0Y, 0Z		
L	L	Н	L	2	2X, 2Y	0X, 1Y, 0Z		
L	L	Н	Н	3	3X, 3Y	1X, 1Y, 0Z		
L	Н	L	L	4	—	0X, 0Y, 1Z		
L	Н	L	Н	5	—	1X, 0Y, 1Z		
L	Н	Н	L	6	—	0X, 1Y, 1Z		
L	Н	Н	Н	7	_	1X, 1Y, 1Z		
Н	Х	Х	Х	None	None	None		

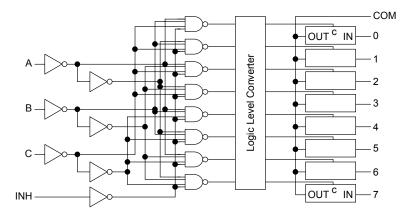
X: Don't care

\*: Except HC4052A

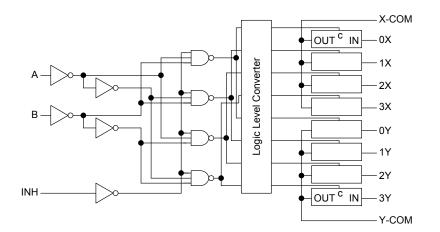
TOSHIBA

### System Diagram

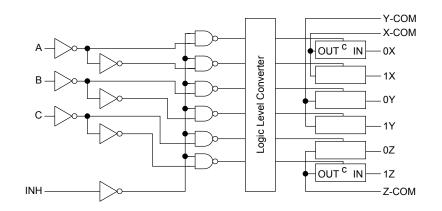
TC74HC4051A



TC74HC4052A



#### TC74HC4053A



### Absolute Maximum Ratings (Note 1)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	–0.5 to 7	V
Supply voltage range	V <sub>CC</sub> -V <sub>EE</sub>	-0.5 to 13	V
Control input voltage	V <sub>IN</sub>	-0.5 to V <sub>CC</sub> + 0.5	V
Switch I/O voltage	V <sub>I/O</sub>	$V_{\mbox{\scriptsize EE}}-0.5$ to $V_{\mbox{\scriptsize CC}}+0.5$	V
Control input diode current	I <sub>ICK</sub>	±20	mA
I/O diode current	I <sub>OK</sub>	±20	mA
Switch through current	Ι <sub>Τ</sub>	±25	mA
DC V <sub>CC</sub> or ground current	ICC	±50	mA
Power dissipation	PD	500 (DIP) (Note 2)/180 (SOP, TSSOP)	mW
Storage temperature	T <sub>stg</sub>	-65 to 150	°C

Note 1: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Note 2: 500 mW in the range of Ta = -40 to 65°C. From Ta = 65 to 85°C a derating factor of -10 mW/°C should be applied up to 300 mW.

#### **Recommended Operating Conditions (Note)**

Characteristics	Symbol	Rating	Unit
Supply voltage range	V <sub>CC</sub>	2 to 6	V
Supply voltage range	V <sub>EE</sub>	-6 to 0	V
Supply voltage range	V <sub>CC</sub> -V <sub>EE</sub>	2 to 12	V
Control input voltage	V <sub>IN</sub>	0 to V <sub>CC</sub>	V
Switch I/O voltage	V <sub>I/O</sub>	V <sub>EE</sub> to V <sub>CC</sub>	V
Operating temperature	T <sub>opr</sub>	-40 to 85	°C
		0 to 1000 (V <sub>CC</sub> = 2.0 V)	
Control input rise and fall time	t <sub>r</sub> , t <sub>f</sub>	0 to 500 (V <sub>CC</sub> = 4.5 V)	ns
		0 to 400 (V <sub>CC</sub> = 6.0 V)	

Note: The recommended operating conditions are required to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

## **Electrical Characteristics**

#### **DC Characteristics**

Characteristics Symb		Test Condi		dition		Ta = 25°C			Ta = -40 to 85°C		
			$V_{EE}(V)$	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Unit	
				2.0	1.50		_	1.50	_		
High-level control input voltage	V <sub>IHC</sub>	—		4.5	3.15			3.15	—	V	
1				6.0	4.20		—	4.20	—		
				2.0	—	—	0.50	—	0.50		
Low-level control input voltage	VILC	_		4.5	—	—	1.35	—	1.35	V	
				6.0	_	—	1.80	—	1.80		
		$V_{IN} = V_{ILC} \text{ or } V_{IHC}$	GND	4.5	—	85	180	—	225		
		$V_{I/O} = V_{CC}$ to $V_{EE}$	-4.5	4.5	—	55	120	—	150		
		$I_{I/O} \leq 2 \ mA$	-6.0	6.0	_	50	100	—	125		
ON resistance	R <sub>ON</sub>	$V_{IN} = V_{ILC} \text{ or } V_{IHC}$ $V_{I/O} = V_{CC} \text{ or } V_{EE}$ $I_{I/O} \le 2 \text{ mA}$	GND	2.0	—	150	—	—	—	Ω	
			GND	4.5	—	70	150	—	190		
			-4.5	4.5	—	50	100	—	125		
		1/0 = 2 11/4	-6.0	6.0	_	45	80	—	100		
Difference of ON	ΔR <sub>ON</sub>	$V_{IN} = V_{ILC} \text{ or } V_{IHC}$	GND	4.5	—	10	30	—	35		
resistance between		$V_{I/O} = V_{CC}$ to $V_{EE}$	-4.5	4.5	—	5	12	—	15	Ω	
switches		$I_{I/O} \leq 2 \ mA$	-6.0	6.0	_	5	10		12		
Input/output leakage		$V_{OS} = V_{CC} \text{ or } GND$	GND	6.0			±60		±600		
current	IOFF	$V_{IS} = GND \text{ or } V_{CC}$	-6.0	6.0			±100		±1000	nA	
(switch off)		$V_{IN} = V_{ILC} \text{ or } V_{IHC}$	-0.0	0.0			100		1000		
Switch input leakage		$V_{OS} = V_{CC}$ or GND	GND	6.0	_		±60		±600		
current (switch on)	IIZ	$V_{IN} = V_{ILC} \text{ or } V_{IHC}$	-6.0	6.0	_		±100		±1000	nA	
, ,				6.0			10.1		110		
Control input current	I <sub>IN</sub>	$V_{IN} = V_{CC}$ or GND	GND	6.0	_		±0.1		±1.0	μA	
Quiescent supply current	ICC	$V_{IN} = V_{CC}$ or GND	GND	6.0	_		4.0		40.0	μA	
Ganoni			-6.0	6.0	_		8.0	—	80.0	μ	

### AC Characteristics (C<sub>L</sub> = 50 pF, input: $t_r = t_f = 6 \text{ ns}$ , GND = 0 V)

Characteristics	Symbol		Test Cor	Test Condition		-	Ta = 25°(	2	Ta –40 to	Unit	
Characteristics	Symbol			V <sub>EE</sub> (V)	V <sub>CC</sub> (V)	Min	Тур.	Max	Min	Max	Onit
				GND	2.0	_	25	60	_	75	
Phase difference				GND	4.5	_	6	12	_	15	
between input and output	Φι/Ο	All types		GND	6.0	_	5	10	_	13	ns
				-4.5	4.5		4	_	_	_	
				GND	2.0	_	64	225	_	280	
				GND	4.5	_	18	45	_	56	
		4051	(Note 1)	GND	6.0	_	15	38	_	48	
				-4.5	4.5		18	_	_	_	
				GND	2.0	_	64	225	_	280	
	t <sub>pZL</sub>			GND	4.5	_	18	45	_	56	
Output enable time	t <sub>pZH</sub>	4052	(Note 1)	GND	6.0	_	15	38	_	48	ns
				-4.5	4.5		18	_	_	_	
				GND	2.0	_	50	225	_	280	
				GND	4.5	_	14	45	_	56	
		4053	(Note 1)	GND	6.0	_	12	38	_	48	
				-4.5	4.5		14	_	_	_	
	<sup>t</sup> pLZ t <sub>pHZ</sub>	4051	(Note 1)	GND	2.0		100	250	_	315	ns
				GND	4.5	_	33	50	_	63	
				GND	6.0	_	28	43	_	54	
				-4.5	4.5		29	_	_	_	
		4052	(Note 1)	GND	2.0	_	100	250	_	315	
<b>.</b>				GND	4.5	_	33	50	_	63	
Output disable time				GND	6.0	_	28	43	_	54	
				-4.5	4.5		29	_	_	_	
			(Note 1)	GND	2.0	_	95	225	_	280	
				GND	4.5	_	30	45	_	56	
		4053		GND	6.0	_	26	38	_	48	
				-4.5	4.5		26	_	_	_	
Control input capacitance	C <sub>IN</sub>	All types		_		_	5	10	_	10	pF
		4051				_	36	70	_	70	
COMMON terminal capacitance	C <sub>IS</sub>	4052		-5.0	5.0	_	19	40	_	40	pF
capacitatice		4053				_	11	20	_	20	
		4051				_	7	15	_	15	
SWITCH terminal capacitance	C <sub>OS</sub>	4052		-5.0	5.0	_	7	15	_	15	pF
capacitance		4053				_	7	15	_	15	
Feedthrough capacitance		4051				_	0.95	2	_	2	
	C <sub>IOS</sub>	4052		-5.0	5.0	_	0.85	2	_	2	pF
		4053				_	0.75	2	_	2	
		4051					70	_	_	_	
Power dissipation	C <sub>PD</sub>	4052	(Note 2)	GND	5.0	_	71	_	_	_	pF
capacitance		4053	. ,			_	67	_	_	_	

Note 1:  $R_L = 1 \ k\Omega$ 

Note 2: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance of IC which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}$ 

#### Analog Switch Characteristics (GND = 0 V, Ta = 25°C) (Note 1)

		Test C		Тур.				
Characteristics	Symbol							Unit
Sine wave distortion		$R_L = 10 \ k\Omega$ ,	V <sub>IN</sub> = 4	4.0 V <sub>p-p</sub>	-2.25	2.25	0.025	
(T.H.D)		$C_L = 50 \text{ pF}$	$V_{IN} = 8.0 V_{p-p}$		-4.5	4.5	0.020	%
(1.11.0)		f <sub>IN</sub> = 1 kHz	$V_{IN} = 1$	11.0 V <sub>p-p</sub>	-6.0	6.0	0.018	
			All	(Note 2)			120	
			4051	(Note 3)	-2.25	2.25	45	
			4052		-2.25	2.25	70	
		Adjust f <sub>IN</sub> voltage to obtain	4053				95	
		OdBm at V <sub>OS</sub>	All	(Note 2)			190	
Frequency responce	f <sub>max</sub>	Increase $f_{IN}$ frequency until dB meter reads $-3dB$ $R_L = 50 \Omega$ , $C_L = 10 pF$ $f_{IN} = 1 MHz$ , sine wave	4051	(Note 3)	-4.5	4.5	70	MHz
(switch on)			4052				110	
			4053				150	
			All	(Note 2)	-6.0	6.0	200	
			4051	(Note 3)			85	
			4052				140	
			4053				190	
		$V_{IN}$ is centered at ( $V_{CC} - V_{EE}$	<u>=</u> )/2		-2.25	2.25	-50	
Feed through attenuation		Adjust input for 0dBm			-2.25	4.5	_50 _50	dB
(switch off)		$\text{R}_{\text{L}}=\text{600}~\Omega,~\text{C}_{\text{L}}=\text{50}~\text{pF}$			- <del>4</del> .5	6.0	-50 -50	ав
		$f_{IN} = 1 \text{ MHz}$ , sine wave			-0.0	0.0	-00	
Crosstalk		$R_{I} = 600 \Omega, C_{I} = 50 pF$			-2.25	2.25	60	
(control input to signal output)		$f_{IN} = 1$ MHz, square wave (	'tr = tr =	6 ns)	-4.5	4.5	140	mV
(control input to orginal output)			(q – q –	0 1.0)	-6.0	6.0	200	
Crosstalk		Adjust $V_{\mbox{\scriptsize IN}}$ to obtain 0dBm at input					-50	
(between any switches)		$R_L=600~\Omega,~C_L=50~pF$	-4.5	4.5	-50	dB		
(		$f_{IN} = 1 \text{ MHz}$ , sine wave			-6.0	6.0	-50	

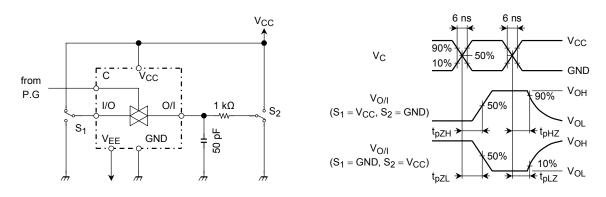
Note 1: These characteristics are determined by design of devices.

Note 2: Input COMMON terminal, and measured at SWITCH terminal.

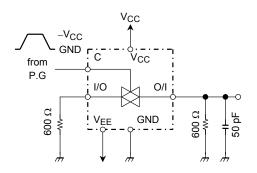
Note 3: Input SWITCH terminal, and measured at COMMON terminal.

### **Switching Characteristics Test Circuits**

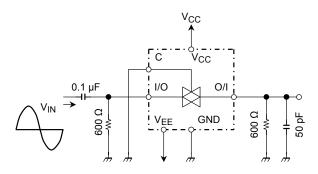
1.  $t_{pLZ}$ ,  $t_{pHZ}$ ,  $t_{pZL}$ ,  $t_{pZH}$ 



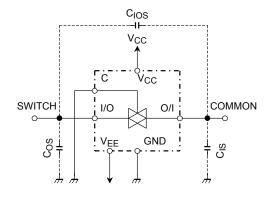
2. Cross Talk (control input-switch output)  $f_{IN} = 1$  MHz duty = 50%  $t_r = t_f = 6$  ns



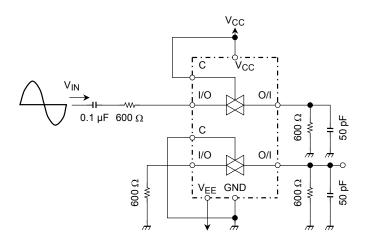
3. Feedthrough Attenuation



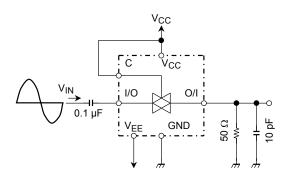
 $4. \quad C_{IOS}, C_{IS}, C_{OS}$ 



#### 5. Cross Talk (between any two switches)



## 6. Frequency Response (switch on)



3.3±0.3

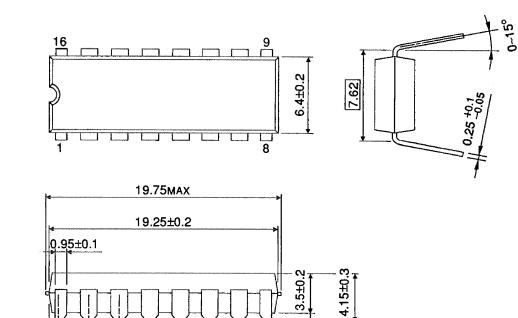
0.51 MIN

0.5±0.1 0.25 0

# Package Dimensions

DIP16-P-300-2.54A

Unit : mm



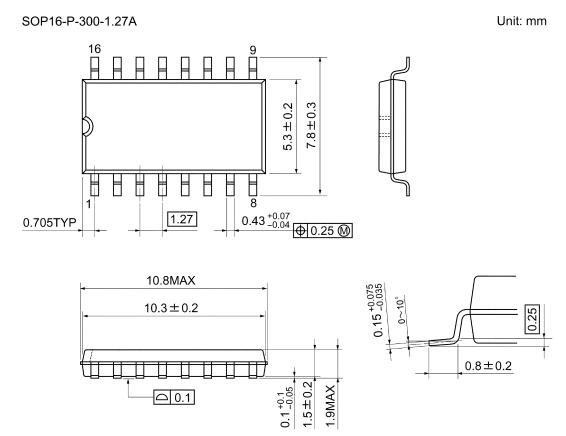
1.4±0.1

Weight: 1.00 g (typ.)

0.735түр

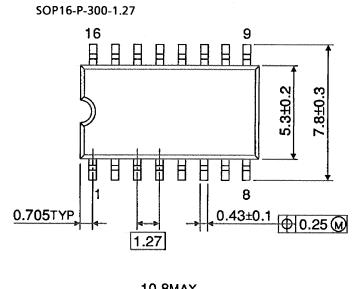
2.54

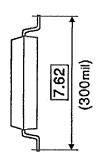
#### **Package Dimensions**



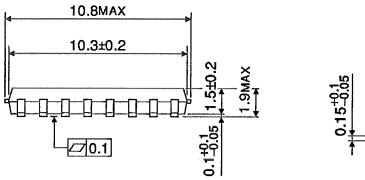
Weight: 0.18 g (typ.)

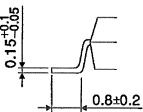
### **Package Dimensions**





Unit : mm



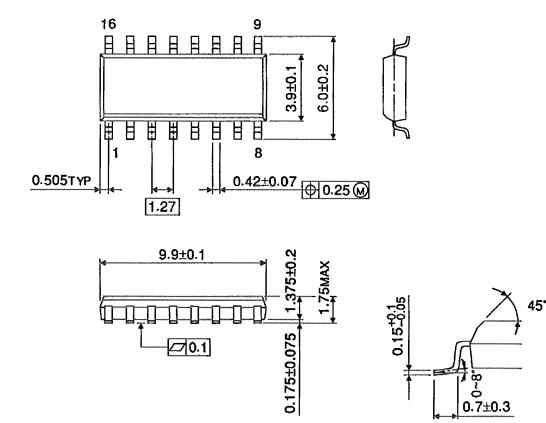


Weight: 0.18 g (typ.)

## Package Dimensions (Note)

SOL16-P-150-1.27

Unit : mm



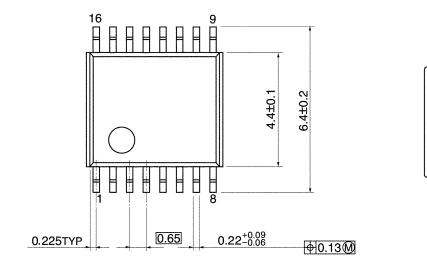
Note: This package is not available in Japan.

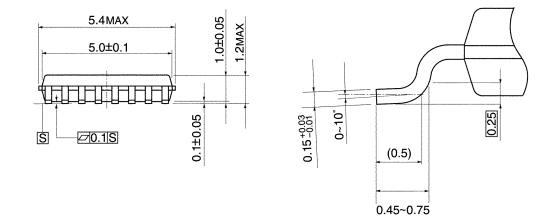
Weight: 0.13 g (typ.)

# Package Dimensions

TSSOP16-P-0044-0.65A

Unit: mm





Weight: 0.06 g (typ.)

Note: Lead (Pb)-Free Packages

DIP16-P-300-2.54A SOP16-P-300-1.27A SOL16-P-150-1.27 TSSOP16-P-0044-0.65A

#### **RESTRICTIONS ON PRODUCT USE**

Handbook" etc. 021023 A

060116EBA

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